

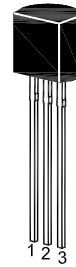
ST 2SC3330

NPN Silicon Epitaxial Planar Transistor

for switching and AF amplifier applications.

The transistor is subdivided into five groups, R, O, Y, G and L, according to its DC current gain.

On special request, these transistors can be manufactured in different pin configurations.



1. Emitter 2. Collector 3. Base
TO-92 Plastic Package

Absolute Maximum Ratings ($T_a = 25^\circ\text{C}$)

Parameter	Symbol	Value	Unit
Collector Base Voltage	V_{CBO}	60	V
Collector Emitter Voltage	V_{CEO}	50	V
Emitter Base Voltage	V_{EBO}	5	V
Collector Current	I_C	200	mA
Power Dissipation	P_{tot}	300	mW
Junction Temperature	T_j	150	$^\circ\text{C}$
Storage Temperature Range	T_{stg}	- 55 to + 150	$^\circ\text{C}$

Characteristics at $T_a = 25^\circ\text{C}$

Parameter	Symbol	Min.	Typ.	Max.	Unit	
DC Current Gain at $V_{CE} = 6\text{ V}$, $I_C = 1\text{ mA}$ Current Gain Group	R	h_{FE}	40	-	80	-
	O	h_{FE}	70	-	140	-
	Y	h_{FE}	120	-	240	-
	G	h_{FE}	200	-	400	-
	L	h_{FE}	350	-	700	-
Collector Base Cutoff Current at $V_{CB} = 40\text{ V}$	I_{CBO}	-	-	0.1	μA	
Emitter Base Cutoff Current at $V_{EB} = 3\text{ V}$	I_{EBO}	-	-	0.1	μA	
Collector Base Breakdown Voltage at $I_C = 100\text{ }\mu\text{A}$	$V_{(BR)CBO}$	60	-	-	V	
Collector Emitter Breakdown Voltage at $I_C = 10\text{ mA}$	$V_{(BR)CEO}$	50	-	-	V	
Emitter Base Breakdown Voltage at $I_E = 10\text{ }\mu\text{A}$	$V_{(BR)EBO}$	5	-	-	V	
Collector Emitter Saturation Voltage at $I_C = 100\text{ mA}$, $I_B = 10\text{ mA}$	$V_{CE(sat)}$	-	0.15	0.3	V	
Gain Bandwidth Product at $V_{CE} = 6\text{ V}$, $I_C = 10\text{ mA}$	f_T	-	200	-	MHz	
Output Capacitance at $V_{CB} = 6\text{ V}$, $f = 1\text{ MHz}$	C_{ob}	-	2.5	-	pF	
Noise Figure at $V_{CE} = 6\text{ V}$, $I_E = 0.5\text{ mA}$, $f = 1\text{ KHz}$, $R_S = 500\text{ }\Omega$	NF	-	4	-	dB	